RUPTURE DETECTION STRUCTURE FOR SEMICONDUCTOR DEVICE

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Abstract of **JP1163673**

PURPOSE:To easily detect the rupture of the beam part of the title semiconductor acceleration sensor by providing a conduction line part which crosses rupture generation areas inside and outside a beam part functioning as a movable part to the beam part. CONSTITUTION:The conduction line parts 5a and 5b for cantilever beam part rupture detection are made of conductive metal. At the line part 5, a couple of conduction lines 5a1 and 5a1 and a short-circuit line 5a2 which short-circuits a proper position between them are formed in one body. Further, the line part 5b is formed similarly to the line part 5a. If the connection part between the cantilever beam part 1 and overlap part 1b of the semiconductor acceleration sensor which is constituted as mentioned above has a break B1, the line 5a2 is cut away from the lines 5a1 and 5a1. Consequently, both ends of the line part 5a become nonconductive and the break of the connection part between the beam part 1a and overlap part 1b can be detected. Similarly, the break of the connection part of the beam part 1a and a support part 1a is detected from the nonconduction state between both end parts of the line part 5b.